

Product Overview

NVMFS5C680NL: Power MOSFET, Single N-Channel, 60 V, 21 A, 27.5 mΩ

For complete documentation, see the data sheet.

Automotive Power MOSFET in a 5 x 6 mm flat lead package designed for compact and efficient designs and including high thermal performance. Wettable Flank Option available for Enhanced Optical Inspection. AEC-Q101 Qualified MOSFET and PPAP capable suitable for automotive applications.

Features

- Low R_{DS(on)}
- · Low Q_G and Gate capacitance
- Industry standard 5 x 6 mm package Industry
- Best in-class FOM (R_{DS(ON)} x Q_G)
- NVMFS5C680NLWF Wettable Flanks Product
- · AEC-Q101 Qualified and PPAP Capable
- · RoHS Compliant

Applications

- · Reverser Battery protection
- · Switching power supplies
- Power switches (High Side Driver, Low Side Driver, H-Bridges etc.)

Benefits

- · Minimize Conduction Losses
- · Minimize Switching Losses
- Compact Design and Standard footprint for direct drop-in
- Increased efficiency, lower power dissipation
- · Enhanced Optical Inspection

End Products

- · Solenoid Driver ABS, Fuel injection
- Motor Control EPS, Wipers, Fans, Seats, etc.
- · Load Switch ECU, Chassis, Body

Part Electrical Specifications																
Product	Compliance	Status	Chan nel Polari ty	Confi gurati on	V _{(BR)D} SS Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	$R_{DS(on)}$ Max @ V_{GS} = 2.5 V (m Ω)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5 V$ (m Ω)	$R_{DS(on)}$ Max @ V_{GS} = 10 V (m Ω)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Pack age Type
NVMFS5C680NLT1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	N- Chan nel	Singl e	60	20	2.2	21	24	-	43	27.5	2.9	5.8	330	SO- 8FL / DFN- 5
NVMFS5C680NLWFT1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	N- Chan nel	Singl e	60	20	2.2	21	24	-	43	27.5	2.9	5.8	330	SO- 8FL / DFN- 5

For more information please contact your local sales support at www.onsemi.com.

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